

SMD VCXO SPECIFICATIONS

Customer	
Customer P/N	
Product	5032 VCXO
Nominal Frequency	24.000000MHz
HOSONIC P/N	D5SV24E000000E
Version	10C0
Issue Date	2026/9/24

HOSONIC		
Drawn	Checked	Approved
LUCY	Richard	JOHN

Approved By Customer : _____

✓ **MSL: Level 1**✓ **Halogen Free**

I ELECTRICAL PARAMETERS

No.	Item	Symb.	Electrical Specification				Remark
			Min.	Typ.	Max.	Units	
1	Nominal Frequency	F0	24.000000				MHz
2	Frequency Calibration		-15		15	ppm	At 25
3	Temperature Stability		-25		25	ppm	Over T _{OPR} , Ref. to 25
4	Stability vs. power change		-5		5	ppm	V _{DD} 5%
5	Stability vs. load change		-3		3	ppm	Cload 10%
6	Pullability		-180		100	ppm	Over Control Voltage range
			-100		180		
7	Control Voltage range		0		3.3	V	
8	Operating Temperature Range	T _{OPR}	-40		85		
9	Storage Temperature	T _{STG}	-55		125		
10	Power supply Voltage	V _{DD}	3.3 5%				V
11	Aging Per Year	Fa	-3		3	ppm	First Year
12	Supply current	I _{DD}			30	mA	
13	Output symmetry	Sym	45		55	%	
14	Rise time	Tr			5	nS	20%~80%V _{DD}
	Fall time	Tf			5	nS	80%~20%V _{DD}
15	Output voltage	V _{OH}	90%			V _{DD}	
		V _{OL}			10%	V _{DD}	
16	Output load HCMOS load	CL			15	pF	
17	Linearity	Lin			10	%	
18	Start-up time				10	mS	
19	Pin 2, tri-state function	pin 2="High"or "open".....output active at pin 4 pin 2="Low".....high impedance at pin 4 pin 2="Low"&Floating.....unstable at pin4,disallowed for this status					

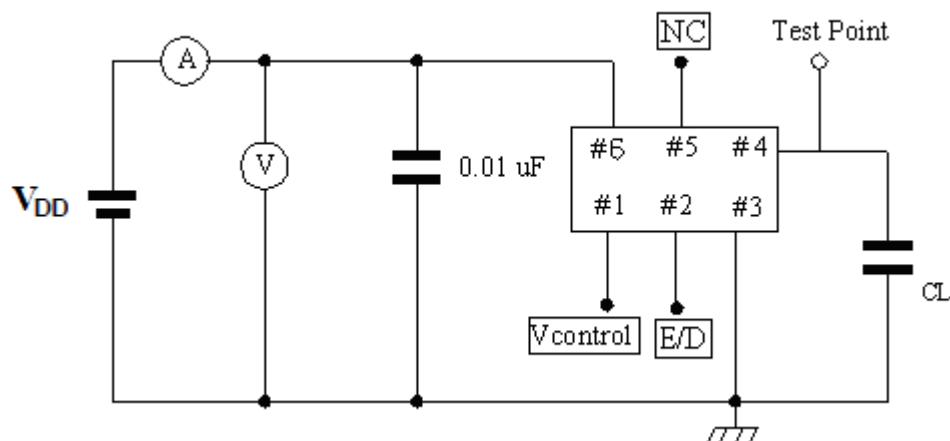
NOTE: Storage Temperature is only for the product itself,the temperature for the packing material is -4~40℃ .

I STORAGE REQUIREMENT

Storage environmental conditions: -4~40 , 70%RH max.

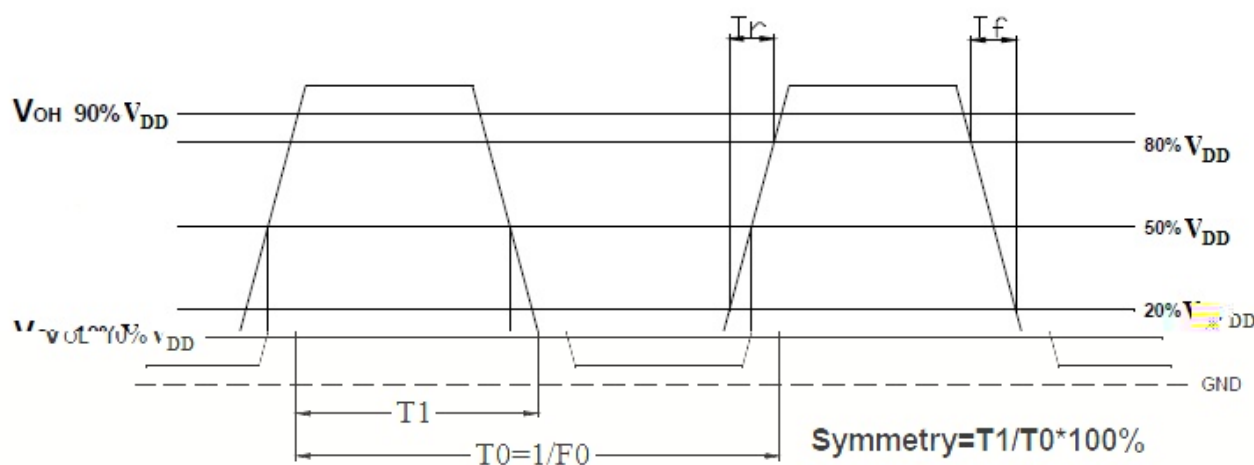
Maximum storage time: 24 Months from date of manufacture.

I HCMOS TEST CIRCUIT

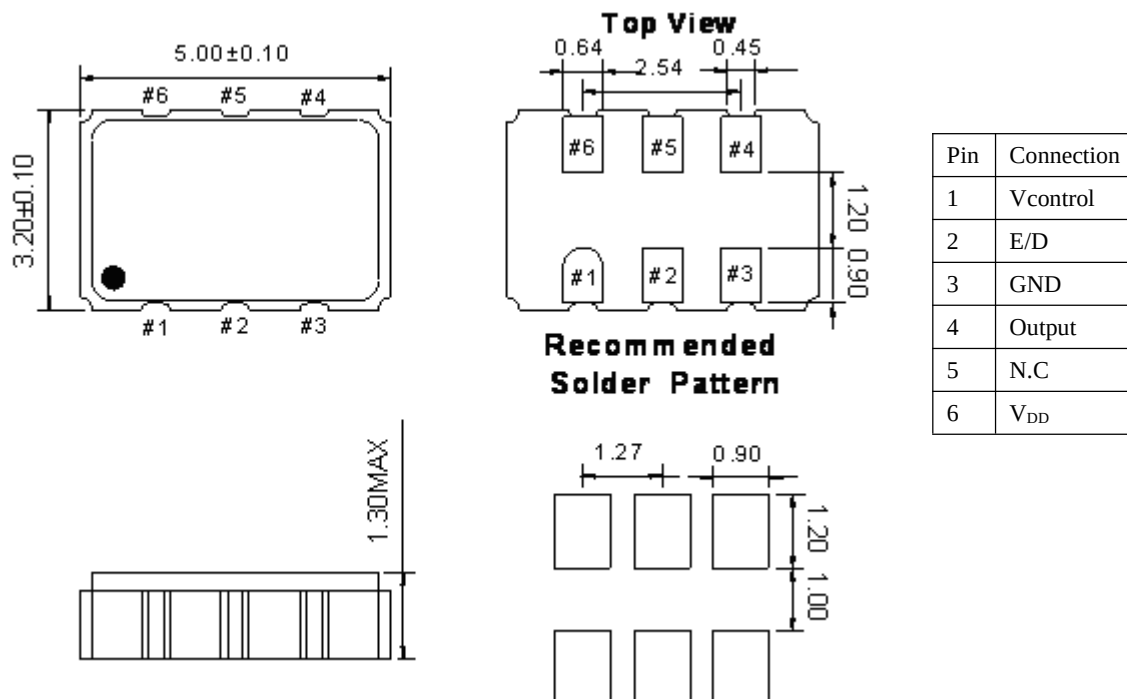


Enable/Disable Function		
Input (pin 2)	Output (pin 4)	Oscillator
Open	Enable	Normal operation
V_{IH} $0.7 \cdot V_{DD} \sim V_{DD}$	Enable	Normal operation
V_{IL} $0V \sim 0.3 \cdot V_{DD}$	Disable	Stop oscillation

I HCMOS OUTPUT WAVEFORM



I OUTLINE DIMENSIONS (unit: mm)

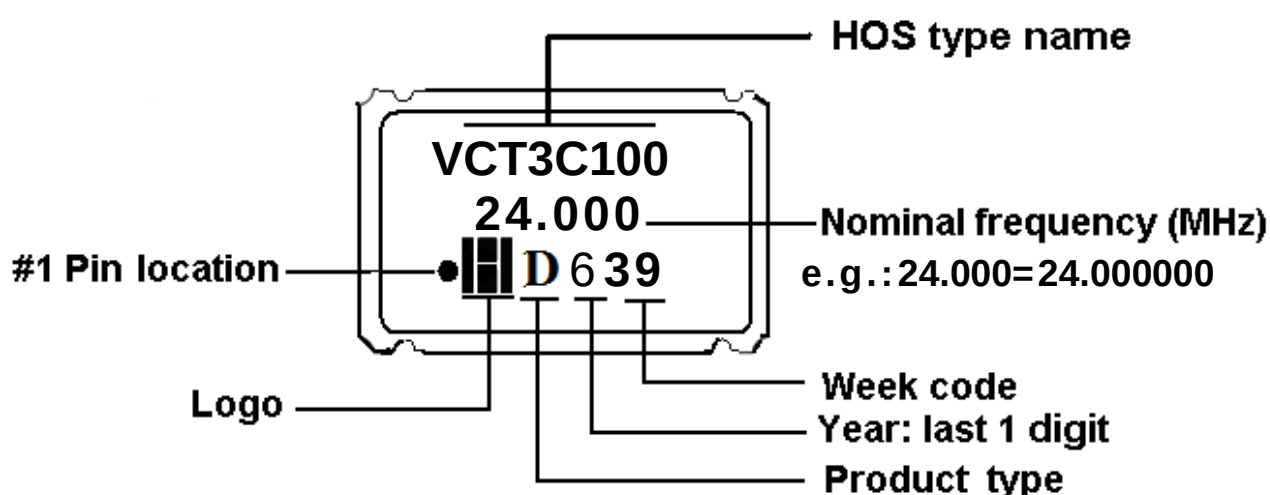


Note 0.01uF bypass capacitor should be placed between V_{DD} (pin 6) and GND (pin 3) to minimize power supply line noise.

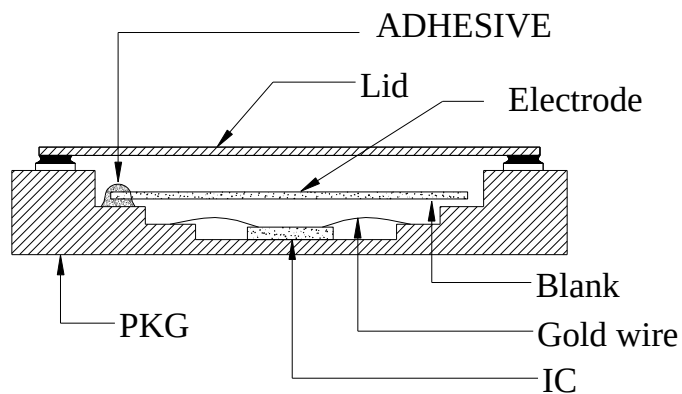
Line shouldn't be layed under the oscillator in the PCB to minimize signal interference.

The Load we advise is only 15pF (that means drive only 1 CMOS/TTL gate).

I MARKING



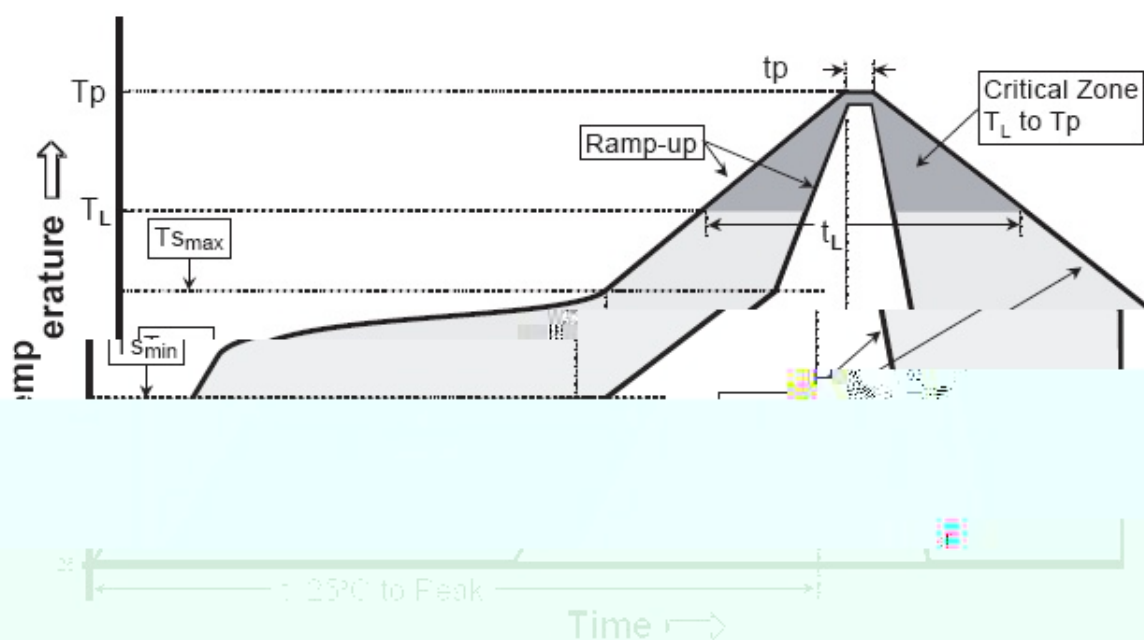
I PRODUCT LAYOUT



NO.	PART	MATERIAL	REMARK
1	LID	KOVAR(Fe+Co+Ni alloy)	
2	PKG	Al ₂ O ₃	Base
3	BLANK	SiO ₂	Quartz
4	ADHESIVE	Ag/SILICON	Support
5	Electrode	Noble metal	
6	IC	Si	
7	Gold wire	Au	Connect

I REFLOW PROFILES

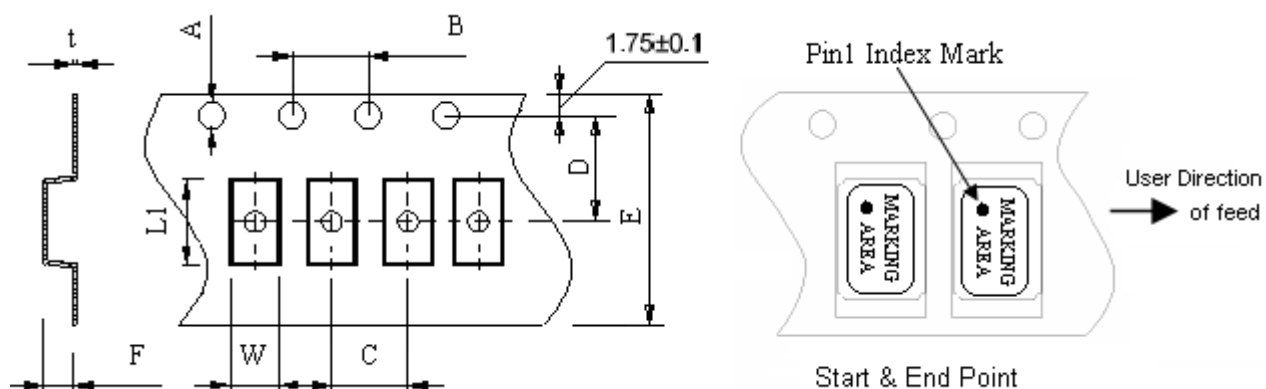
Profiles Feature	Pb-Free Assembly
Average Ramp-up Rate (Ts max to Tp)	3 /second max.
Preheat	
Temperature Min (Ts min)	125
Temperature Max (Ts max)	200
Time (ts min to ts max)	60~180 seconds
Time maintained above	
Temperature (T_L)	217
Time (t_L)	60~150 seconds
Peak/Classification Temperature (T_p)	260
Time within 5 of actual Peak Temperature (t_p)	20~40 seconds
Ramp-down rate	6 /second max.
Time 25 to Peak Temperature	8 minutes max.
Suggest reflow times	3 Times max



Remark: To reference JEDEC J-STD-020

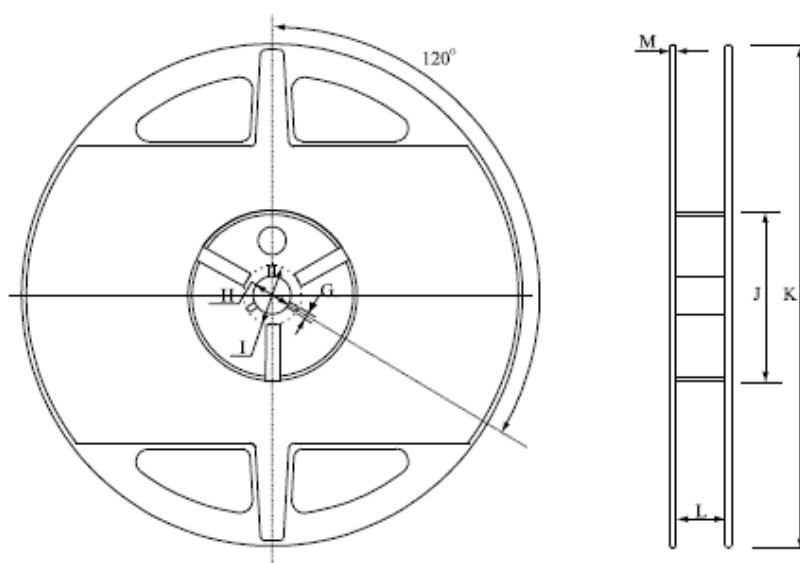
I PACKAGE

Tape Dimensions(unit : mm)



A	B	C	D	E	F	L1	W	t
1.5 ± 0.1	4.0 ± 0.1	8.0 ± 0.1	5.5 ± 0.1	12 ± 0.3	1.5 ± 0.1	5.4 ± 0.1	3.6 ± 0.1	0.30 ± 0.05

Reel Dimensions(unit: mm)



G	H	I	J	K	L	M
2.2 ± 0.5	13.5 ± 0.5	18.2 ± 0.5	60.0 ± 1.0	178.0 ± 1.0	13.5 ± 1.0	1.6 ± 0.2

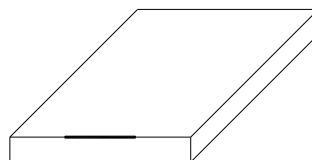
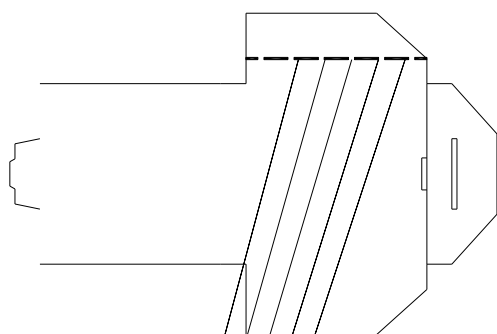
*1000pcs/Reel



HOSONIC TECHNOLOGY (GROUP) CO., LTD.



Carton Dimension (unit : mm)



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I RELIABILITY SPECIFICATIONS

No.	Test Item	Test Conditions	Reference
1	High Temperature Storage	Temperature: 125 3 Time: 1000 12 Hours	MIL-STD-202 Method 108
2	Low Temperature Storage	Temperature: -40 3 Time: 1000 12 Hours Temperature 1: -55 3 Temperature 2: 125 3	JIS-C7021 B-12
3	Temperature Cycle	Temperature change between T1 and T2 at soonest Run 1000 cycles, maintain T1 and T2 15minutes each in one cycle	JESD22 Method JA-104
4	Solder Heat Resistance	Pre-heat: 125 60~120 Seconds Solder Temperature: 260 5 Time: 30 Seconds	MIL-STD-202 Method 210
5	Drop Test	3 Times Free Fall from 75cm height to concrete floor.	IEC 60068-2-32
6	High Temperature, High Humidity Storage	Temperature: 85 5 Relative Humidity: 80%--85% Time: 250Hours 12 Hours	MIL-STD-202 Method 1

I 应用注意事项 APPLICATION NOTES:

1. soldering

7 reflow Please adhere to the standard temperature curve for soldering. The soldering temperature for quartz crystal products must be carefully controlled, as excessive temperature or prolonged exposure can result in significant frequency drift. For guidance, please refer to the reflow curve provided on page 7.

2. / Cleaning/Coating

2.1 PH

The use of a general cleaning solution (pH neutral) and ultrasonic cleaning is acceptable; however, this applies only to single products. The results obtained from testing should be verified in accordance with the actual usage conditions.

2.2 ! " # \$ % & ' () * + , - , . / 0 1 2 , 3 4 5 6 , 7 8 9 : ; < Please evaluate before apply a protective coating on or around the crystal oscillator. Do not use corrosive materials, such as polyurethane glue, which may destroy the seal of the crystal oscillator.

3. PCB => PCB Assembly

3.1 ? @ A B C D ? @ E @ F G , G 8 H I # . J , K L M N O P 6 < > GLASS During the de-boarding process, care must be taken to prevent excessive bending of the board, as this may lead to oscillator failure or poor soldering quality. It is advisable to conduct tests and confirm results beforehand, particularly for GLASS products encapsulated with glass adhesive.

3.2 < > Q E , 8 R S T U 9 : , V W X Y Z # H I , [PCB = > . \] ^ < > Q E The ultrasonic packaging process can inflict damage on the internal circuits of the crystal oscillator due to excessive vibration, potentially affecting its aging characteristics or leading to failure. Therefore, we do not recommend using ultrasonic packaging for crystal PCB assembly.

3.3 C _ < > Q E , 8 ` a b c d e ` , V W X f g , H I # 9 h , [PCB = > E ^ C _ < >) , i j k l m n , o L p The injection molding packaging process exerts significant pressure on the surface of the crystal oscillator, which may alter its s